40V 170A N-Channel Enhancement Mode Power MOSFET

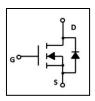
Features

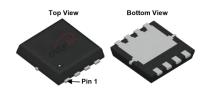
- RDSON \leq 1.8m Ω @Vgs=10V
- Advanced SGT process
- Excellent RDS(ON) and Low Gate Charge
- · Lead free product is acquired

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

SYMBOL







PDFN5*6

ASSEMBLY MESSAGE

| Product Name | Package | Packaging | | |
|--------------|---------|-----------|--|--|
| BXS018N04C | PDFN5*6 | Reel | | |

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

| Parameter | | Symbol | Rating PDFN5*6 | Unit |
|--|-------------------------------------|------------------|----------------|------|
| Drain-Source Voltage | | V _{DSS} | 40 | V |
| Danie Oceano | Continuous (TC = 25°C) | 1- | 170 | А |
| Drain Current | Continuous (T _C = 100°C) | l _D | 141 | А |
| Drain Current | ent Pulsed (Note1) | | 340 | А |
| Single Pulsed Avalanche Energy | | EAS | 180 | mJ |
| Gate-Source Voltage | | V _{GSS} | ±20 | V |
| Power Dissipation T _C =25°C | | P _D | 96 | W |
| Maximum Junction Temperature | | TJ | 150 | °C |
| Storage Temperature Range | | Tstg | -55 to 150 | °C |

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

THERMAL CHARACTERISTICS

| Parameter | Symbol | Max. | Unit | |
|--------------------------------------|-------------------|---------|------|--|
| Farameter | Syllibol | PDFN5*6 | Oill | |
| Thermal Resistance, Junction to Case | R ₀ JC | 1.3 | °C/W | |

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ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

| Parameter | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|--|---------------------|----------------------------|------|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | VGS=0V, ID=250µA | 40 | | | V |
| Zero Gate Voltage Drain Current | IDSS | VDS=40V, VGS=0V | | | 1 | uA |
| Gate-Body Leakage Current, Forward | Igss | VGS=20V | | | 100 | nA |
| Gate-Body Leakage Current, Reverse | | VGS=-20V | | | -100 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | VDS=VGS, ID=250μA | 1.0 | 1.6 | 2.5 | V |
| Drain-Source On-State Resistance | D | VGS=10V, ID=20A | | 1.31 | 1.8 | mΩ |
| Dialii-Source Oil-State Resistance | R _{DS(ON)} | VGS=4.5V, ID=10A | | 1.45 | 2.5 | mΩ |
| DYNAMIC PARAMETERS | | | | | | |
| Input Capacitance | Ciss | VDS=20V, VGS=0V, | | 6350 | | pF |
| Output Capacitance | Coss | | 1126 | | pF | |
| Reverse Transfer Capacitance | Crss | f=1.0MHz | | 39.8 | | pF |
| SWITCHING PARAMETERS | | | | | | |
| Turn-ON Delay Time | t _{D(ON)} | | | 16 | | ns |
| Turn-ON Rise Time | t _R | VDD=20V, ID=20A, VGS | | 8 | | ns |
| Turn-OFF Delay Time | t _{D(OFF)} | = 10V, RG=3Ω 40 | 40 | | ns | |
| Turn-OFF Fall-Time | t _F | | | 60 | | ns |
| Total Gate Charge(Note2) | Q_{G} | \/DC -20\/ \/CC -40\/ | | 89 | | nC |
| Gate Source Charge | Q _{GS} | VDS =20V, VGS =10V, ID=20A | | 14 | | nC |
| Gate Drain Charge | Q _{GD} | | | 8 | | nC |
| SOURCE- DRAIN DIODE RATINGS | AND CHAR | ACTERISTICS | | | | |
| Drain-Source Diode Forward Voltage | V _{SD} | Is=20A, VGS=0V | | | 1.4 | V |
| Diode Continuous Forward Current | Is | | | | 85 | Α |
| Maximum Pulsed Drain to Source Diode Forward Current | Іѕм | | | | 340 | А |

Note: 2. Essentially independent of operating temperature

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TYPICAL CHARACTERISTICS

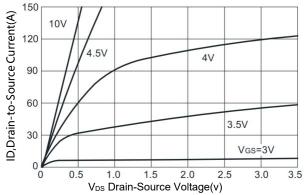


Figure 1. Typical Output Characteristics

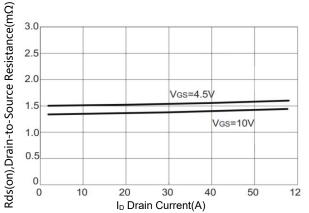


Figure 3. On-Resistance versus Drain Current

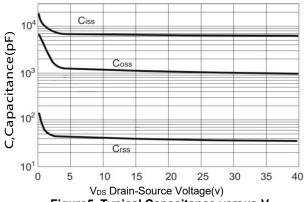


Figure 5. Typical Capacitance versus V_{DS}

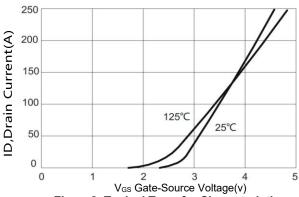


Figure 2. Typical Transfer Characteristics

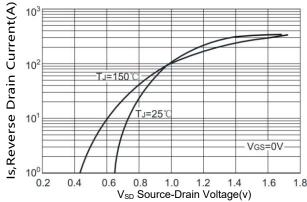


Figure 4. Diode forward voltage versus Current

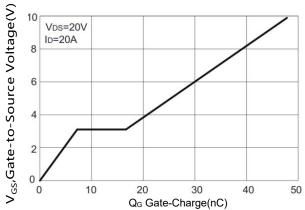


Figure 6. Typical Gate Charge versus V_{GS}

TYPICAL CHARACTERISTICS(Cont.)

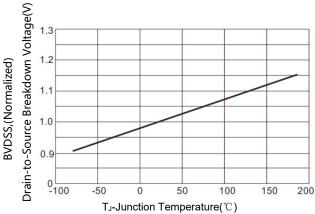


Figure 7. BV_{DSS} Variation with Temperature

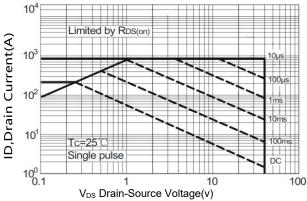


Figure 9. Maximum Safe Operating Area

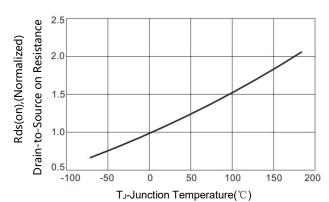


Figure 8. On-Resistance Variation with Temperature

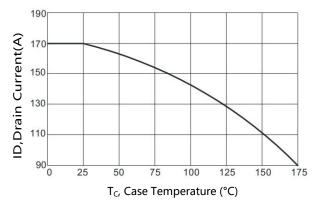
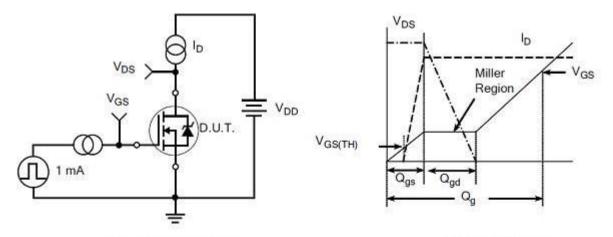
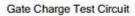


Figure 10. Maximum Continuous Drain Current versus Case Temperature

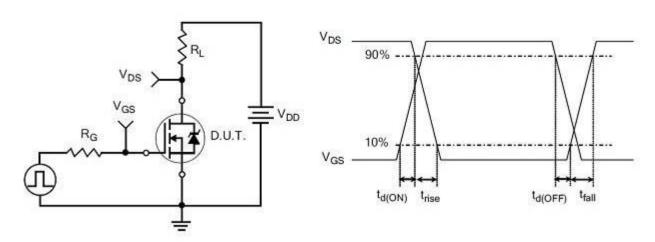


TEST CIRCUITS AND WAVEFORMS





Gate Charge Waveform

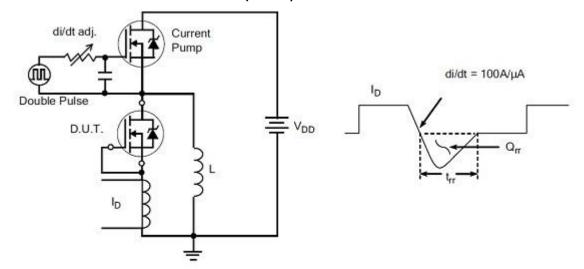


Resistive Switching Test Circuit

Resistive Switching Waveforms

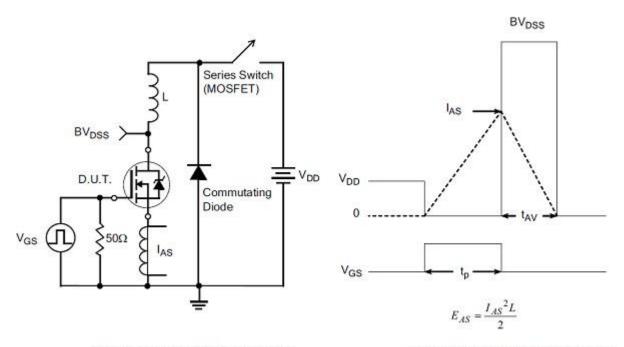


TEST CIRCUITS AND WAVEFORMS(Cont.)



Diode Reverse Recovery Test Circuit

Diode Reverse Recovery Waveform



Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

Revision history

Document revision history

| Date | Revision | Changes |
|-------------|----------|---------------|
| 26-Nov-2021 | 1.0 | First release |
| | | |
| | | |
| | | |

Version: 1.0

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